

## 4.5.4 Pulsed Laser Method

Silver nitrate+ reducing agent -----> Silver nanoparticle

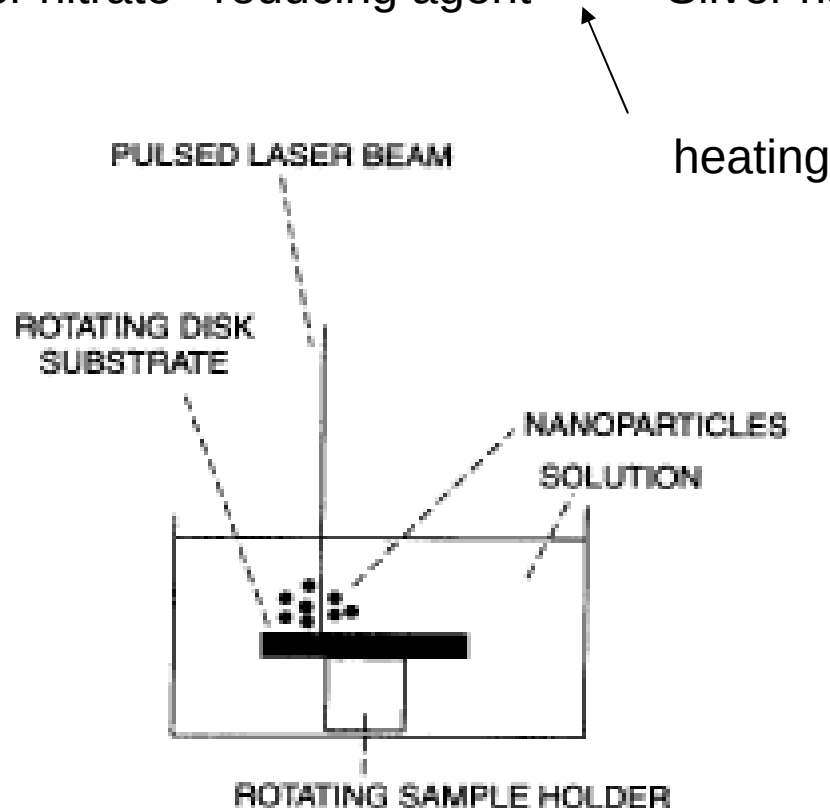
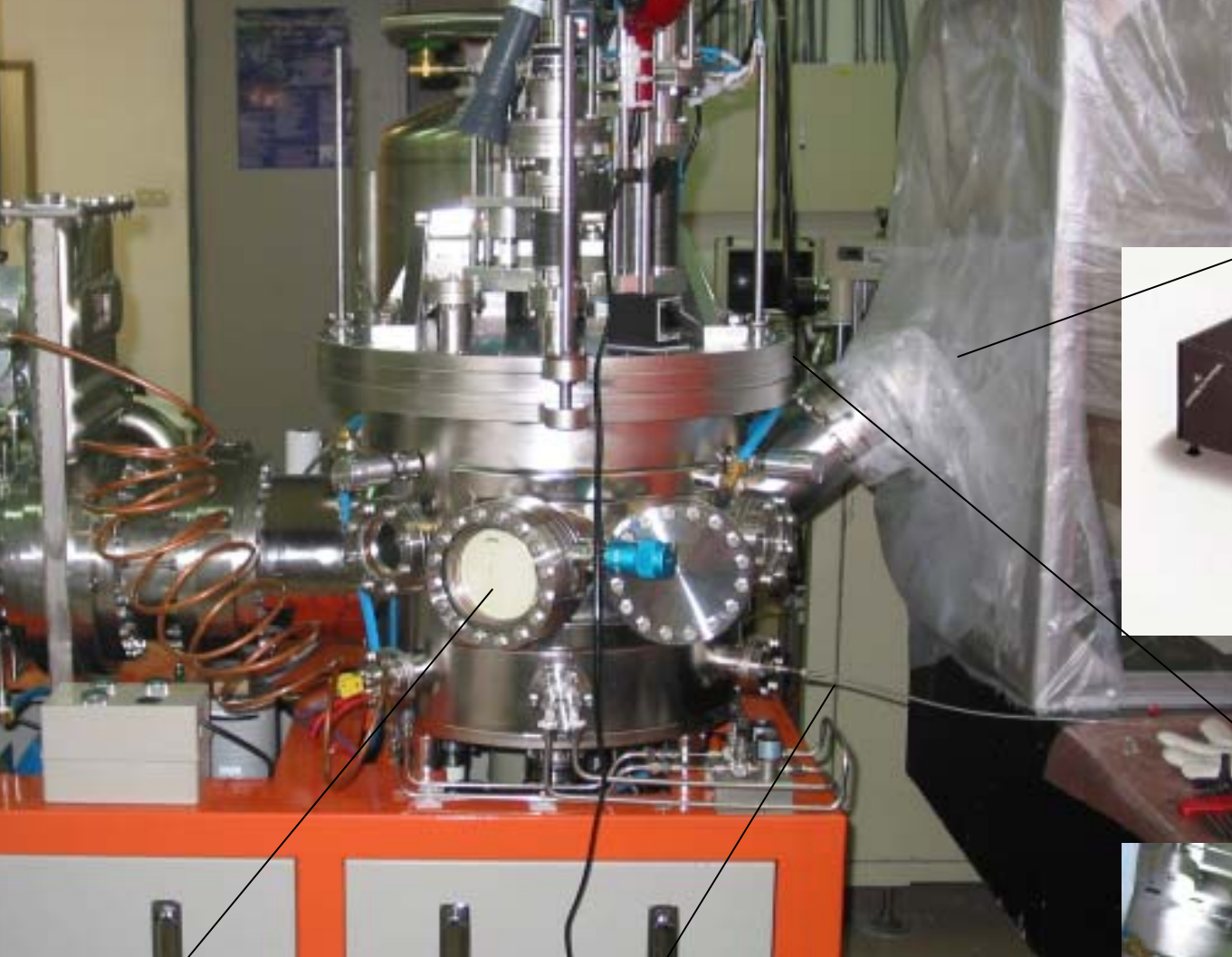


Figure 4.28. Apparatus to make silver nanoparticles using a pulsed laser beam that creates hot spots on the surface of a rotating disk. [Adapted from J. Singh, *Mater. Today* 2, 10 (2001).]

# Laser Ablation

# Laser Ablation





Laser source



RHEED



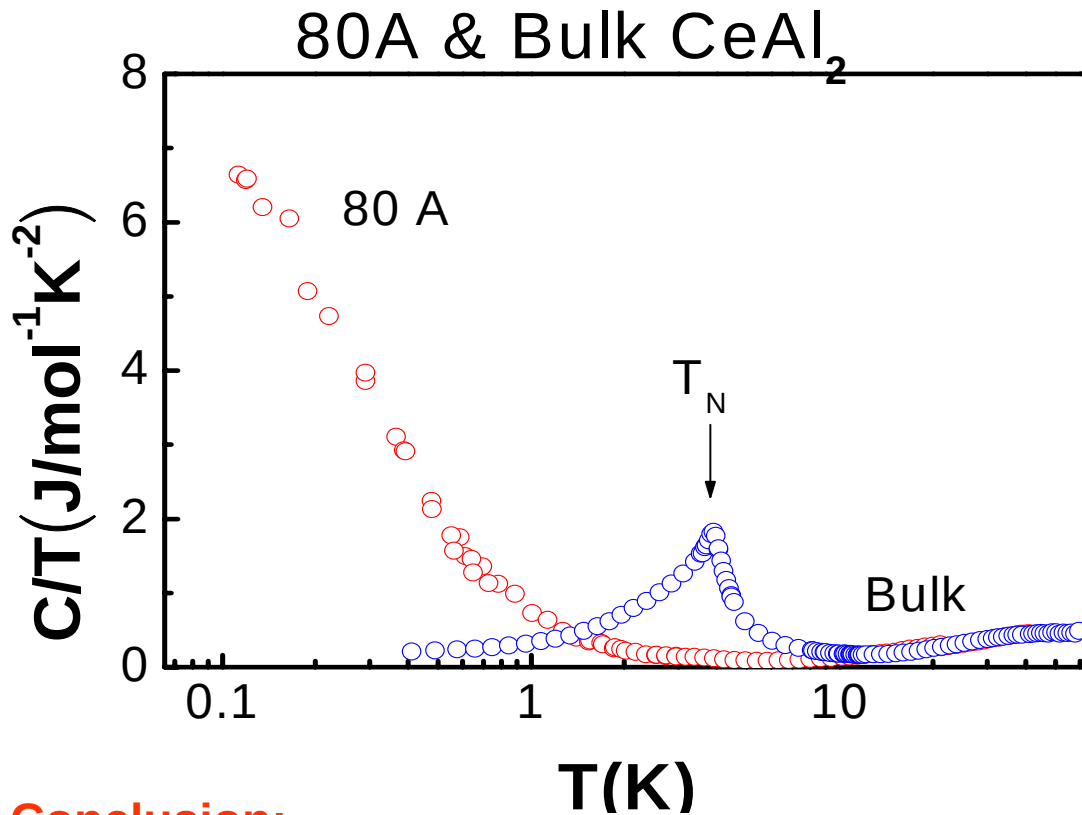
RHEED SCREEN



Plasma monitor



# 1. Quantum size effects on the competition between Kondo interaction and magnetic order in 0-D.



## Conclusion:

In 80A - $\text{CeAl}_2$ , magnetic ordering completely disappears and the  $\gamma$  reaches 9500 mJ/mol Ce  $\text{K}^2$ .

## Unsolved problems:

In nanoparticle, only 0.7 Mole  $\text{Ce}^{3+}$  left, Is the 0.3 mol non-magnetic Ce really on the surface ? or it is just a coincidence.

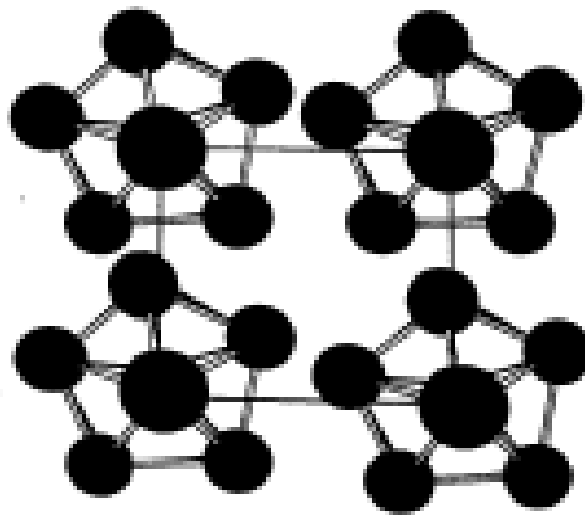
## 4.6 Conclusion

In this chapter a number of examples have been presented showing that the physical, chemical, and electronic properties of nanoparticles depend strongly on the number and kind of atoms that make up the particle. We have seen that color, reactivity, stability, and magnetic behavior all depend on particle size. In some instances entirely new behavior not seen in the bulk has been observed such as magnetism in clusters that are constituted from nonmagnetic atoms. Besides providing new

# Chapter 6 Bulk Nanostructured Materials

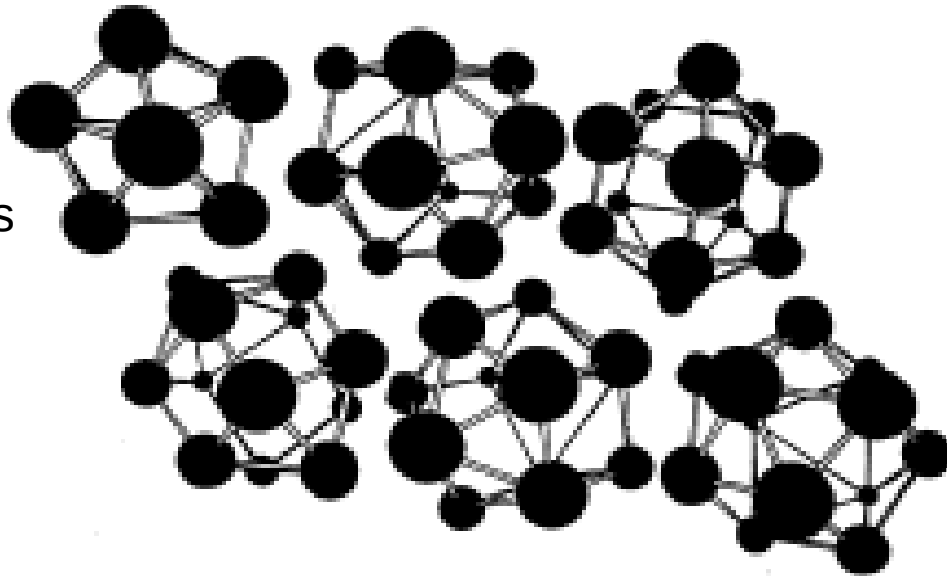
- Bulk nanostructured materials are solid
- having
  1. a nanosized microstructure
  2. the basic units are nanoparticles

Hypothetical 2-D  
Ordered  $\text{Al}_{12}$  particles  
forming nanostructure



(a)

Disordered  $\text{Al}_{12}$  Particles



(b)

**Figure 8.1.** (a) Illustration of a hypothetical two-dimensional square lattice of  $\text{Al}_{12}$  particles, and (b) illustration of a two-dimensional bulk solid of  $\text{Al}_{12}$  where the nanoparticles have no ordered arrangement with respect to each other.



# 6.1 Solid disordered nanostructure

- **Compaction and consolidation**
- 1. 85%Cu and 15%Fe powder in atomic weight
- 2. Ball milling to form  $\text{Fe}_{85}\text{Cu}_{15}$  particles
- 3. Compacted using a tungsten-carbide at 1GPa
- 4. Hot compaction at  $\sim 400^\circ\text{C}$  with 870 MPa
- Density 99.2%

# Distribution of size

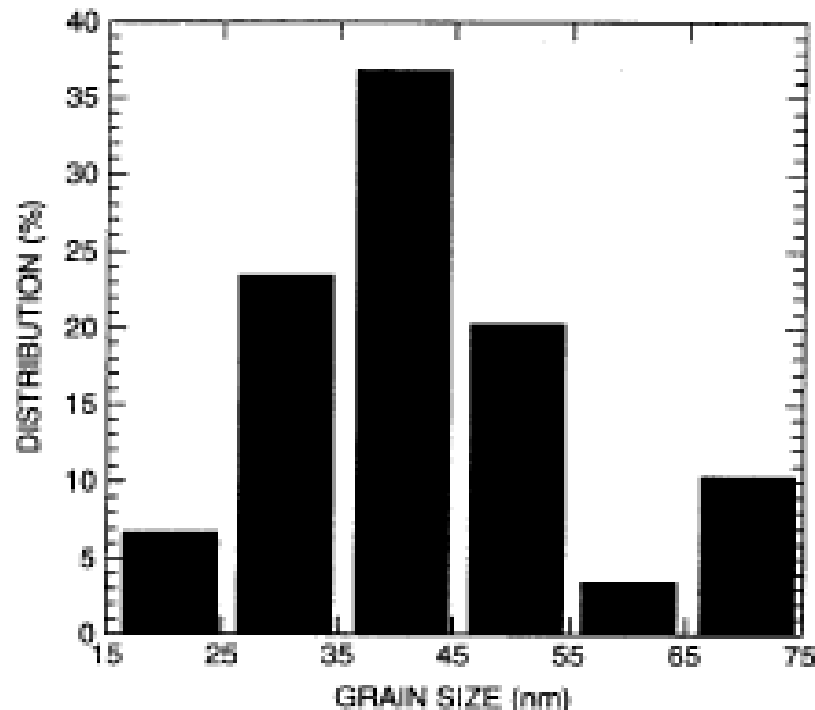
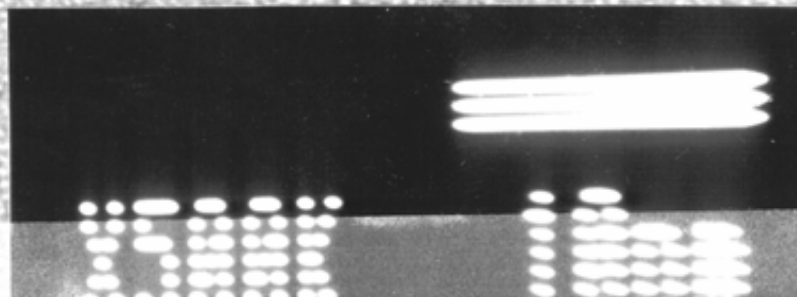
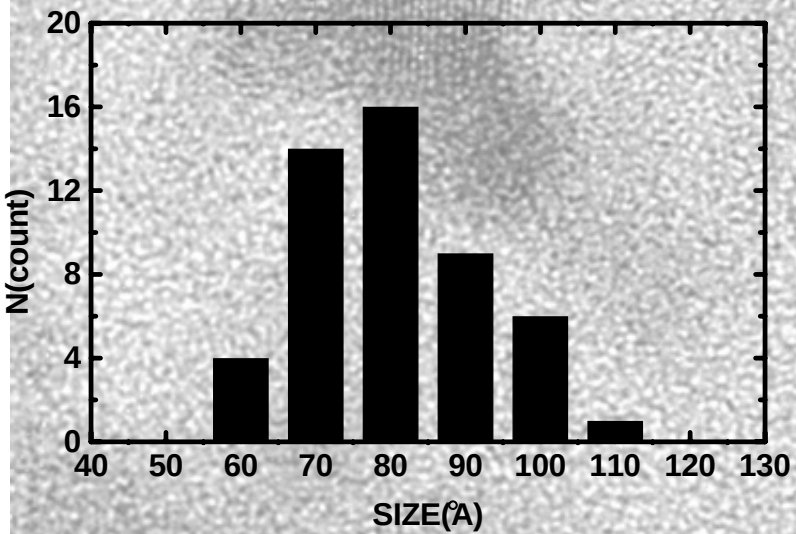
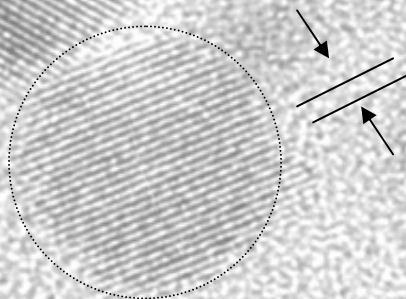


Figure 6.2. Distribution of sizes of Fe-Cu nanoparticles made by hot compaction methods described in the text. [Adapted from L. He and E. Ma, *J. Mater. Res.* 15, 904 (2000).]

# CeAl<sub>2</sub> HRTEM



Fracture stress enhanced from 0.56 GPa (40 nm grain) to 2.8 GPa (50-150  $\mu\text{m}$  grain Iron)

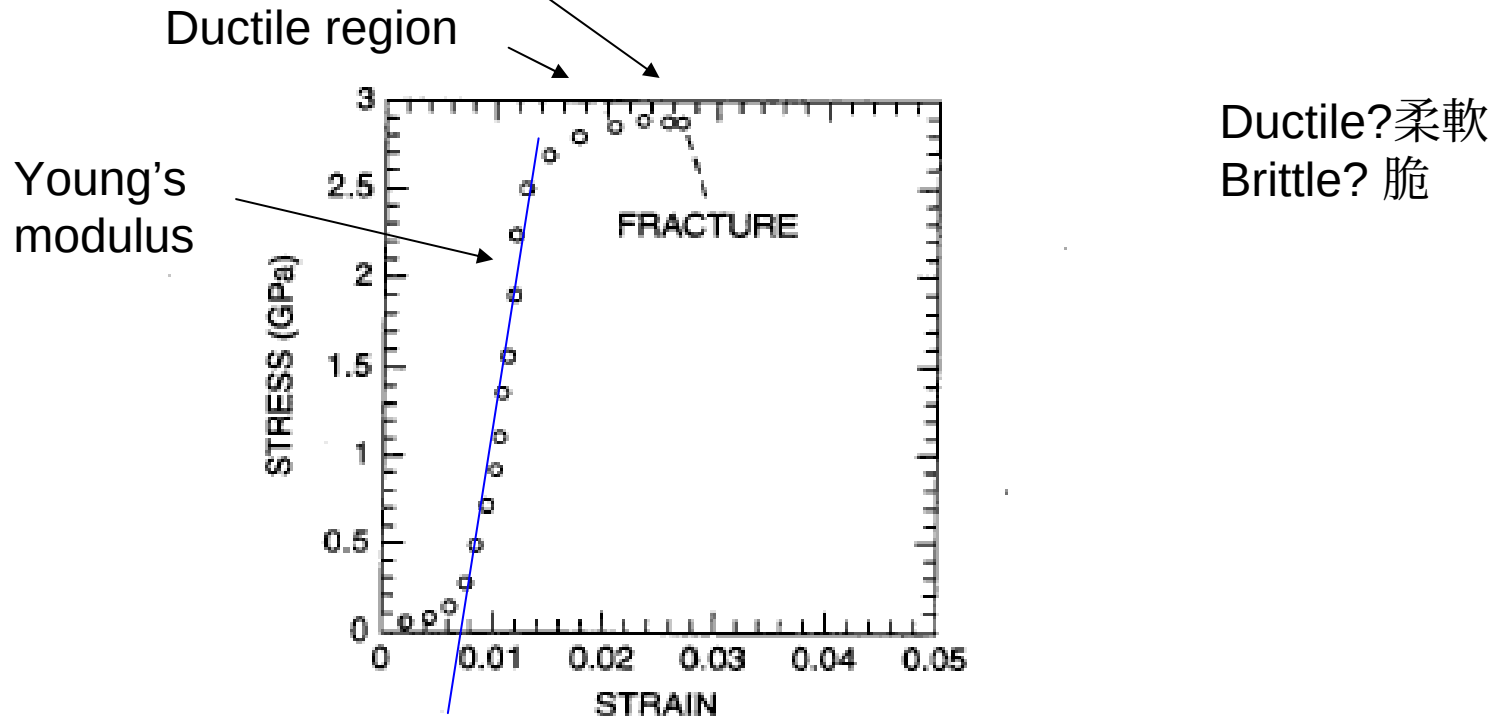
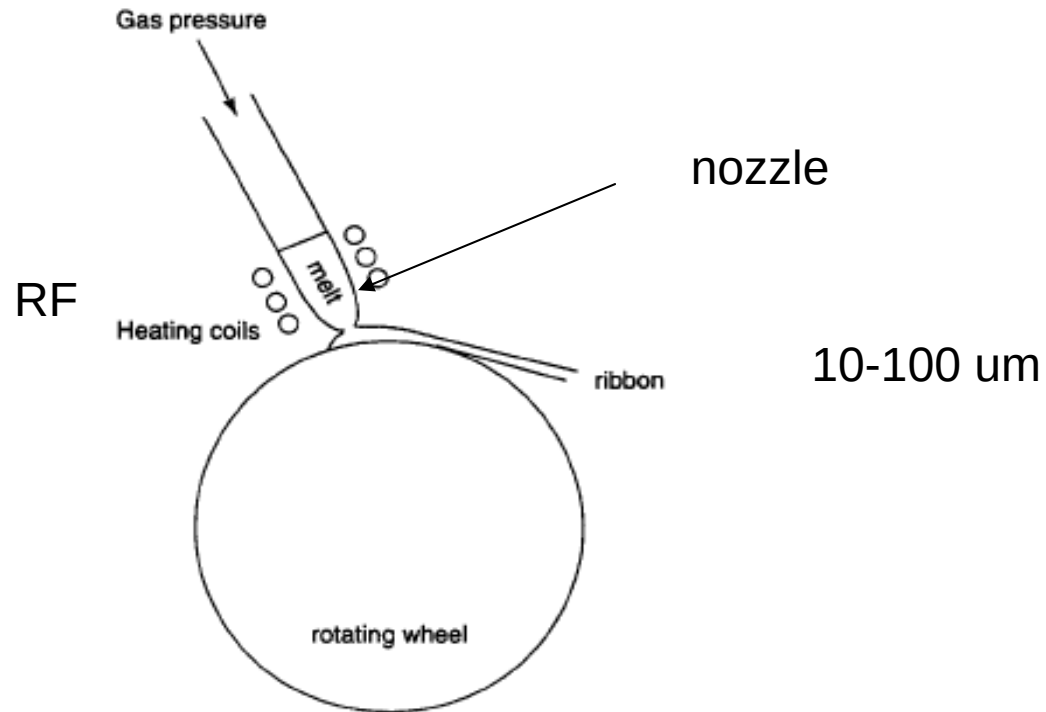


Figure 6.3. Stress-strain curve for bulk compacted nanostructured Fe-Cu material, showing fracture at a stress of 2.8 GPa. [Adapted from L. He and E. Ma, *J. Mater. Res.* 15, 904 (2000).]

# Rapid solidification-Chill block melt spinning

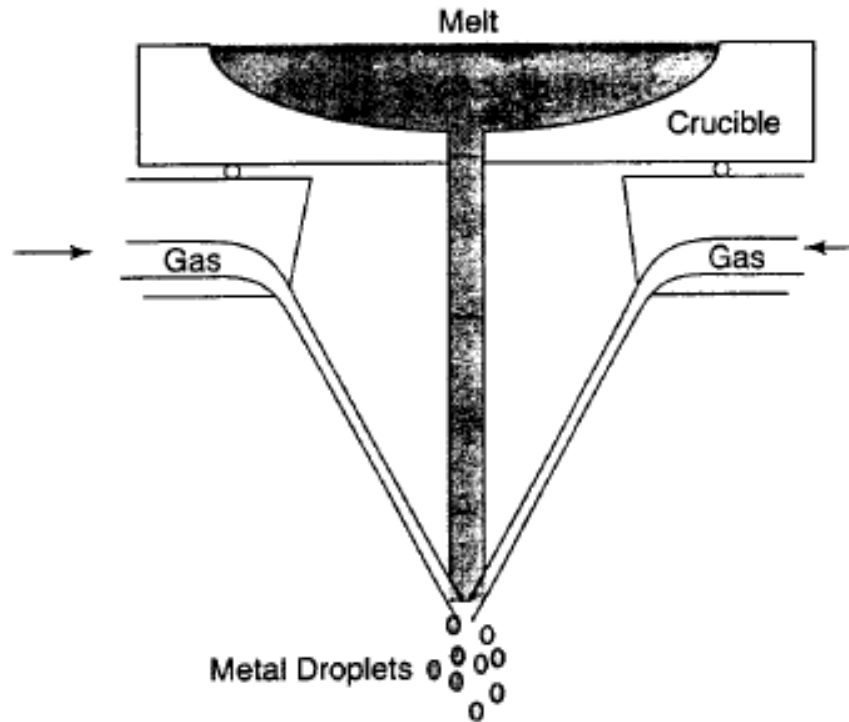


**Figure 6.4.** Illustration of the chill block melting apparatus for producing nanostructured materials by rapid solidification on a rotating wheel. (With permission from I. Chang, in *Handbook of Nanostructured Materials and Nanotechnology*, H. S. Nalwa, ed., Academic Press, San Diego, 2000, Vol. 1, Chapter 11, p. 501.)

## Light weight, high strength materials

- 1. A melt spun alloy Al(85-94%)-Y-Ni-Fe
- 2. Consisting of 10-30 nm Al particles
- 3. Tensile strength  $\sim 1.2$  GPa

# Gas atomization



**Figure 6.5.** Illustration of apparatus for making droplets of metal nanoparticles by gas atomization. (With permission from I. Chang, in *Handbook of Nanostructured Materials and Nanotechnology*, H. S. Nalwa, ed., Academic Press, San Diego, 2000, Vol. 1, Chapter 11, p. 501.)

# Electrodeposition (P137)

- Electrodes
- Electrolyte (電解液)
- Cu 2 mm film with grain size of 27 nm
- Enhanced yield strength 119 MPa



# 6.1.2 Failure mechanisms of conventional grain-sized materials

Crack!

An irreversible elongation after  
breaking of the bond

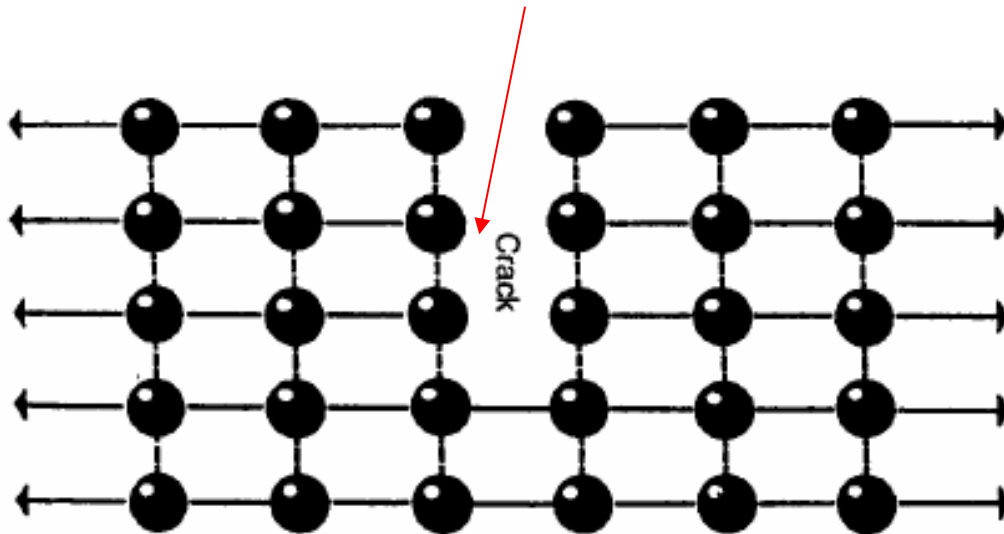
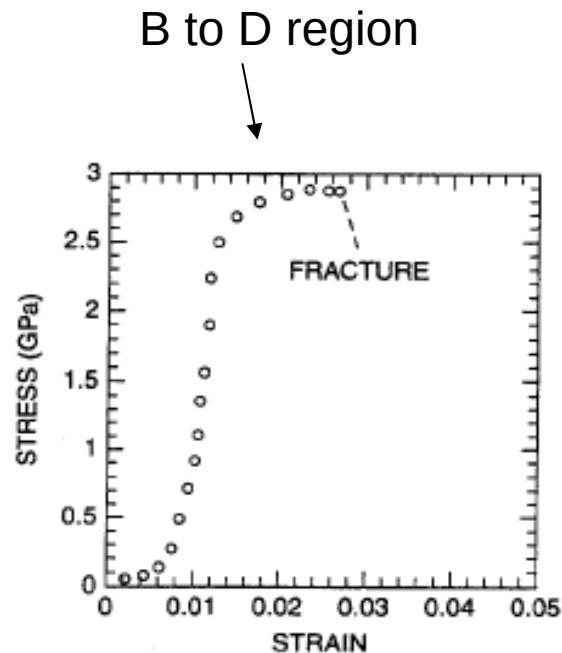


Figure 6.6. A crack in a two-dimensional rectangular lattice.

# Brittle to ductile transition !



Stress-strain curve for bulk compacted nanostructured Fe-0.5C of 2.8 GPa. [Adapted from L. He and E. Ma, *J. Mater.*

Lattice dislocation.

1. Lattice slide
2. Weaker bonds along the dislocation

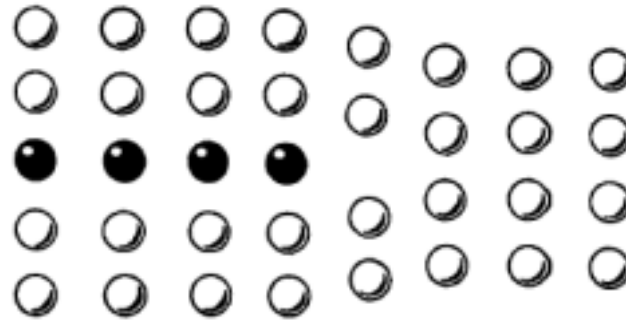


Figure 6.7. An edge dislocation in a two-dimensional rectangular lattice.

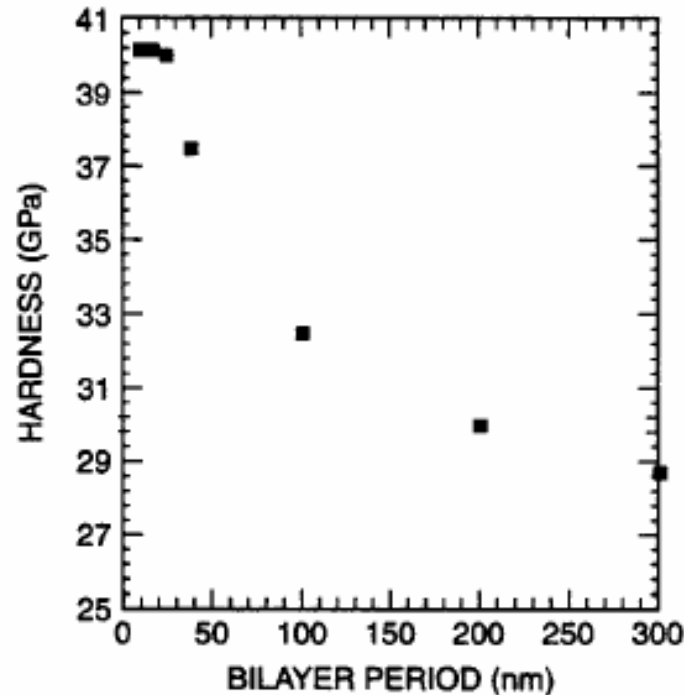
**Hardening:** to Impede the movement of dislocation by introducing tiny particles iron carbide

# 6.1.3 Mechanical Properties

- 1. Young's modulus: stress-strain ratio
- 2. The **yield strength  $s$**  is described by
  - Hall-Petch equation for a conventional grain-size materials
  - **$s = s_0 + K / d^{0.5}$**
  - Materials having smaller grains have more grain boundaries, blocking dislocation movement
- 3. Bulk nanostructured materials are quite brittle and display reduced ductility (~ a few % elongations) for grain size < 30 nm. Due to flaws and porosity

# 6.1.4 Nanostructured multilayers

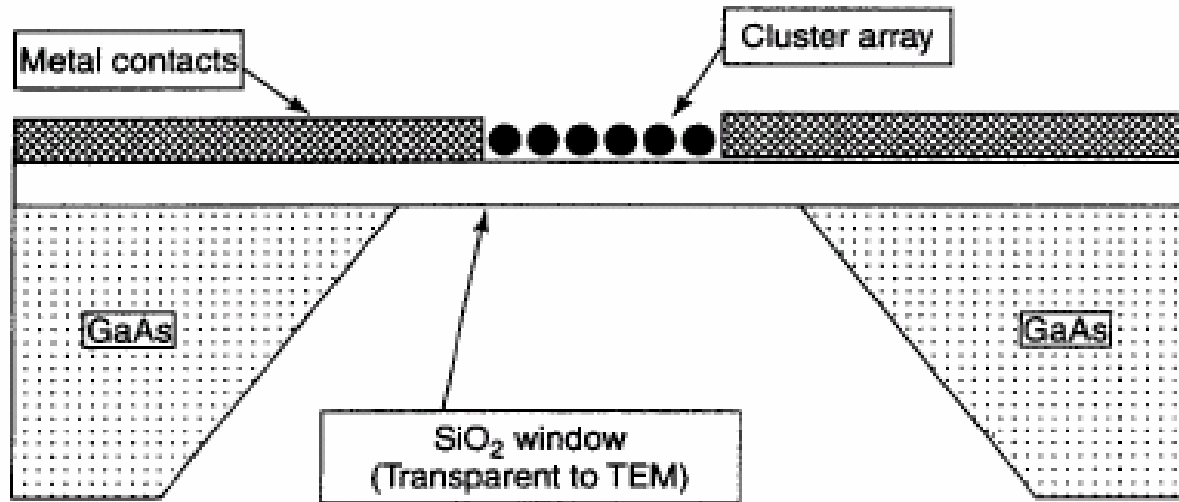
142 BULK NANOSTRUCTURED MATERIALS



**Figure 6.11.** Plot of the hardness of TiN/NbN multilayer materials as a function of the thickness of the layers. (Adapted from B. M. Clemens, MRS Bulletin, Feb. 1999, p. 20.)

Due to Increasing interfaces and structure mismatch

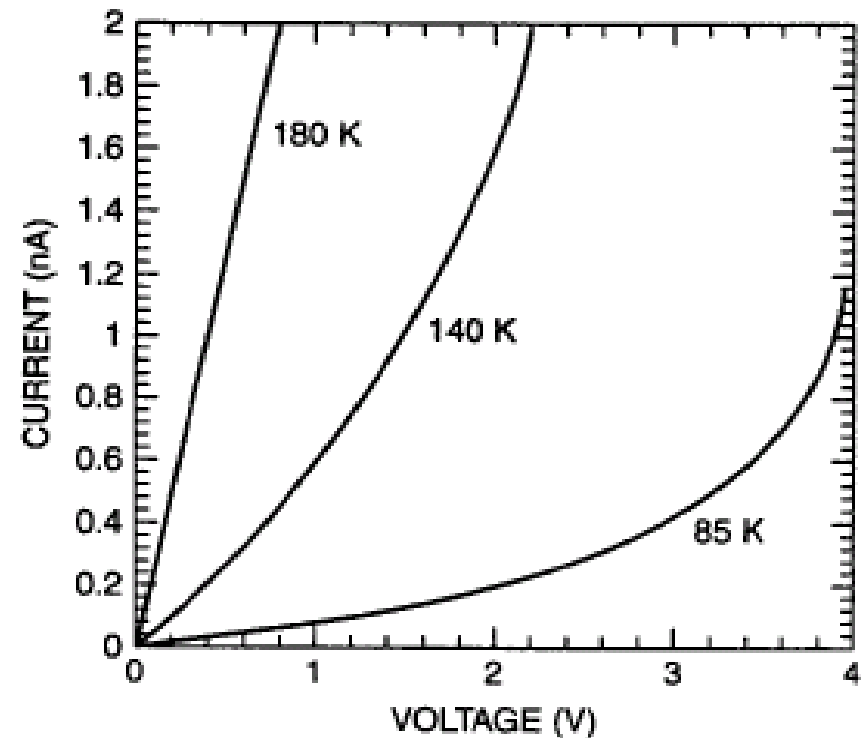
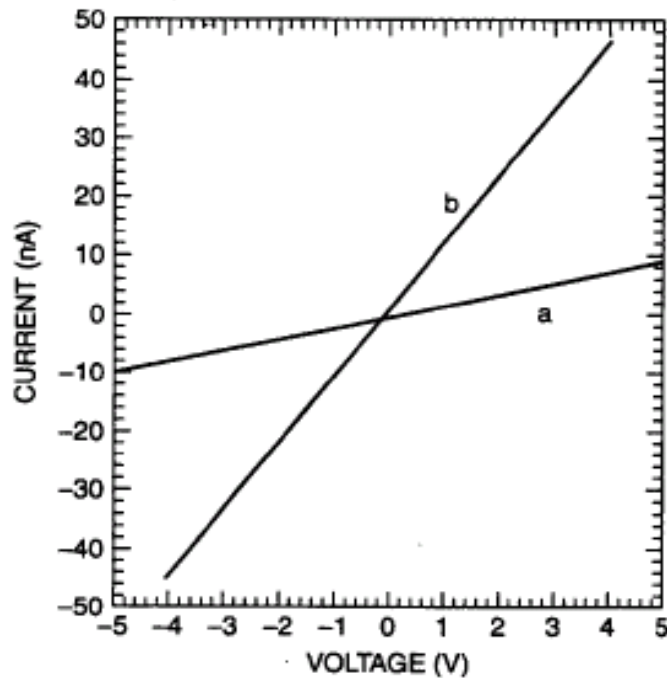
## 6.1.5 Electrical properties



**Figure 6.12.** Cross-sectional view of a lithographically fabricated device to measure the electrical conductivity in a two-dimensional array of gold nanoparticles linked by molecules. (With permission from R. P. Andres et al., in *Handbook of Nanostructured Materials and Nanotechnology*, H. S. Nalwa, ed., Academic Press, San Diego, 2000, Vol. 3, Chapter 4, p. 217.

$$G = G_0 \exp\left(\frac{-E}{k_B T}\right)$$

E: activation energy



room-temperature current-voltage relationship for a two-dimensional  
 kagome lattice (line a) and with the particles linked by a  $(\text{CN})_2\text{C}_{18}\text{H}_{12}$  molecule (line b).  
 James et al., *Superlatt. Microstruct.* **18**, 275 (1995).

# Electron tunneling

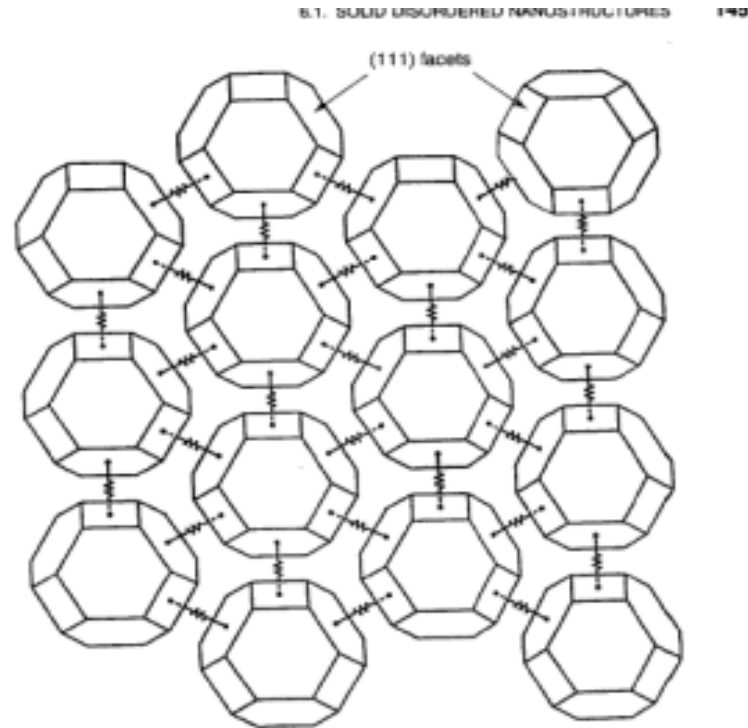
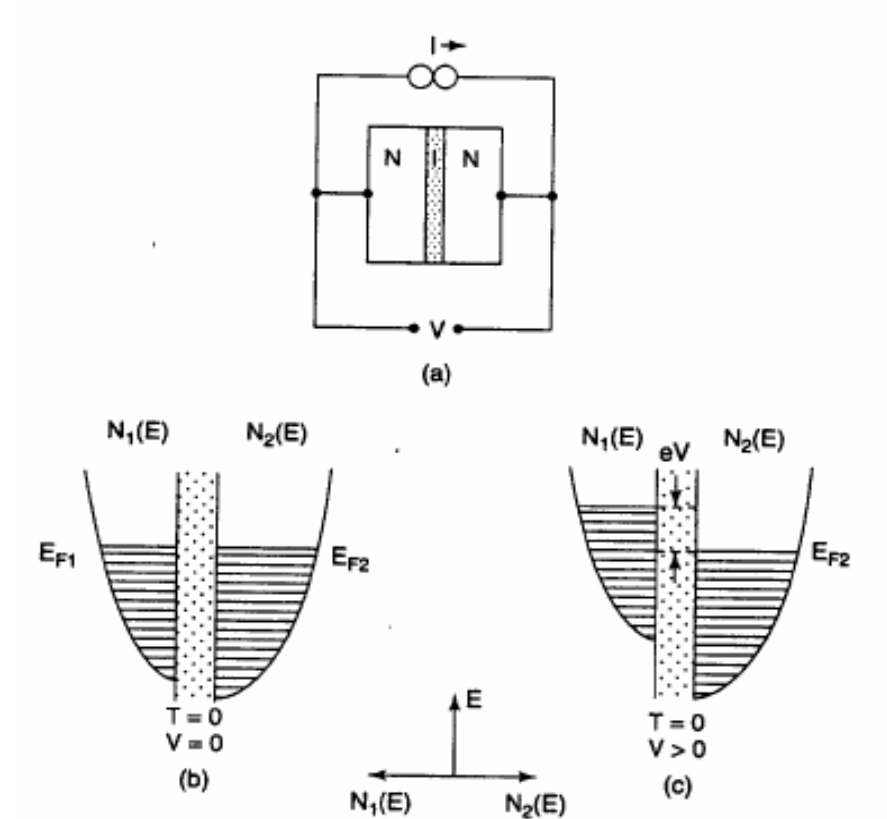


Figure 6.15. Sketch of a model to explain the electrical conductivity in an ideal hexagonal array of single-crystal gold clusters with uniform intercluster resistive linkage provided by resistors



16. (a) Metal-insulator-metal junction; (b) density of states of occupied levels before a voltage is applied to the junction; (c) density of states of occupied levels after a voltage is applied to the junction.

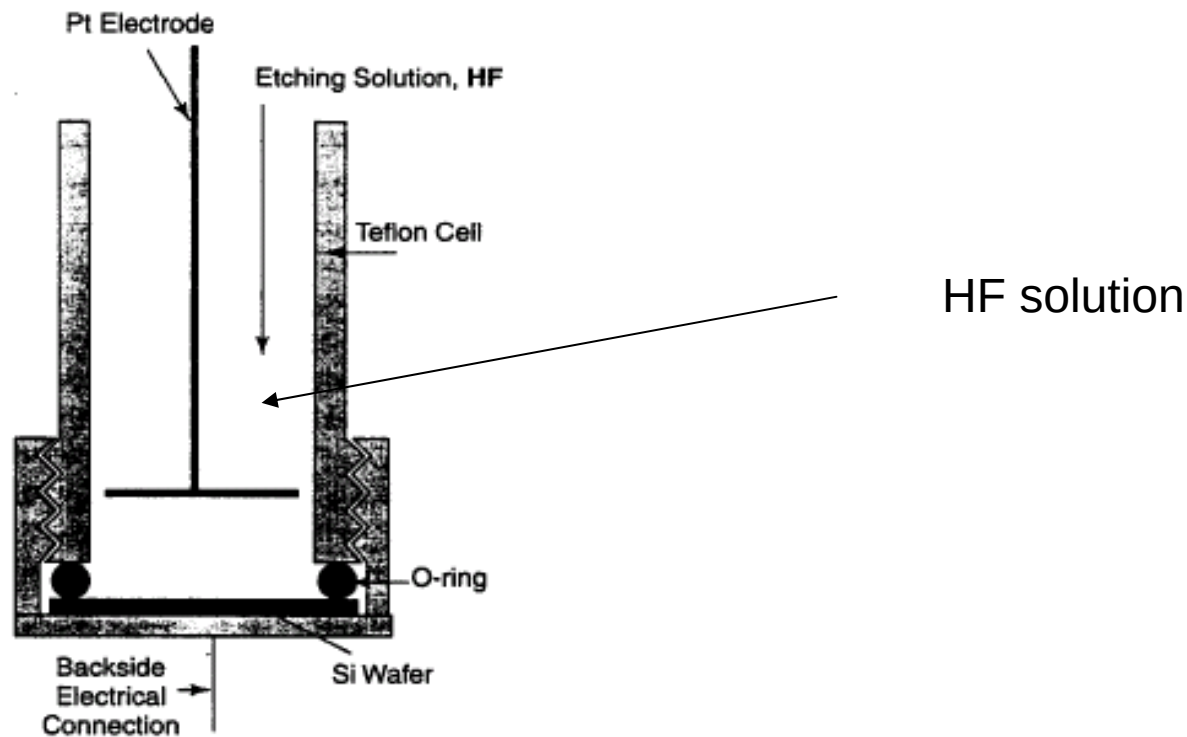
$$N_1(E - eV)f(E - eV)[N_2(E)(1 - f(E))] \quad (6.3) \quad \text{The no. of electrons that can move}$$

$$I = K \int N_1(E - eV)N_2(E)[f(E - eV) - f(E)]dE \quad (6.4) \quad \text{Net Current}$$

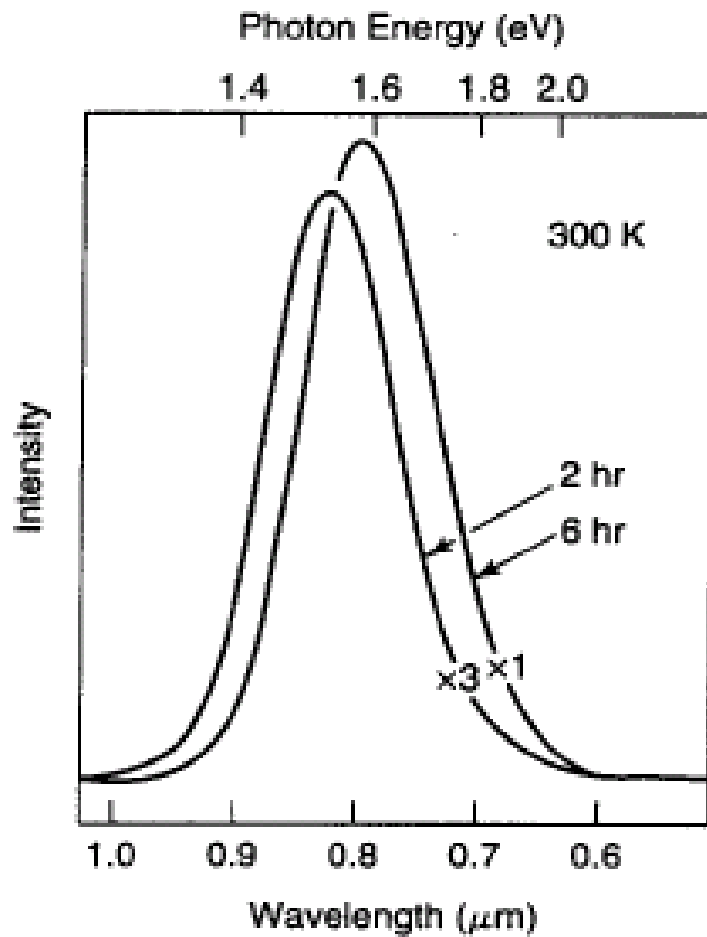
$$G_{nn} = KN_1(E_f)N_2(E_f)e \quad (6.7)$$



## 6.1.8 Porous Silicon made by electrochemical etching in hydrogen fluoride



**6.21.** A cell for etching a silicon wafer in a hydrogen fluoride (HF) solution in order to create pores. (With permission from D. F. Thomas et al., in *Handbook of Nanostructured Materials and Nanotechnology*, H. S. Nalwa, ed., Academic Press, San Diego, 2000, Vol. 4, p. 173.)



luminescence spectra of porous silicon for two different aging times. Note the change in scale for the two curves. [Adapted from]

**Luminescence:** Absorption of energy  
Reemit Visible or near-visible light

**Fluorescence:** emission occurs  
within  $10^{-8}$  s

**Phosphorescence:** a delay emission



# Explanations

p-type silicon is etched, a very fine network of pores having dimensions less than 10 nm is produced.

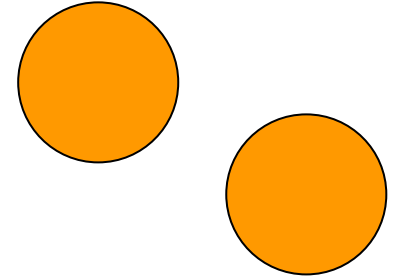
A number of explanations have been offered to explain the origin of the fluorescence of porous silicon, such as the presence of oxides on the surface of the pores that emit molecular fluorescence, surface defect states, quantum wires,

quantum dots and the resulting quantum confinement, and surface states on quantum dots. Porous silicon also displays electroluminescence, whereby the luminescence is induced by the application of a small voltage across electrodes mounted on the silicon, and cathodoluminescence from bombarding electrons.

# Quantum effects 量子效應：

## Quantum size effect

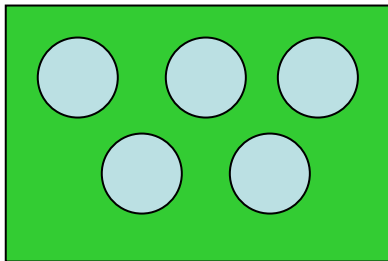
「量子尺寸效應」



Particles, etc

## Quantum confinement effect

「量子侷限效應」

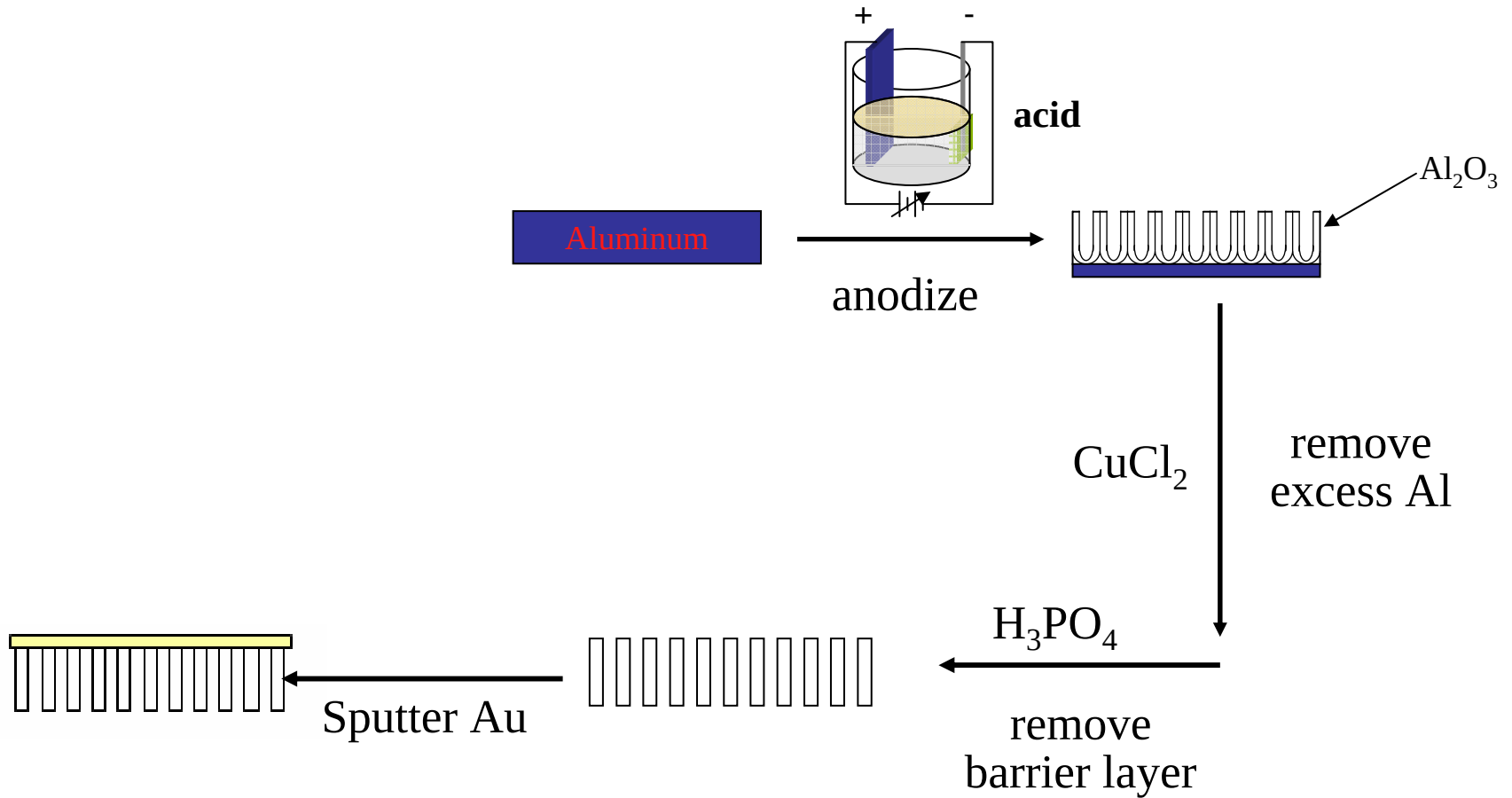


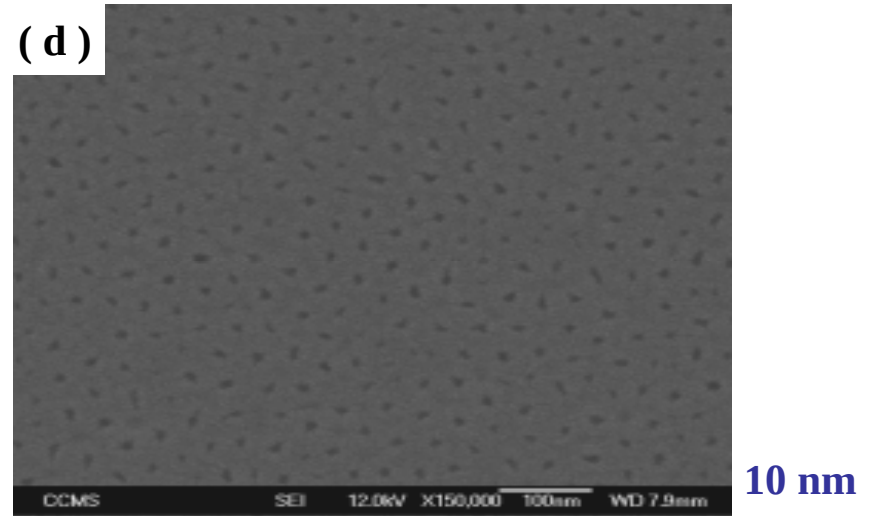
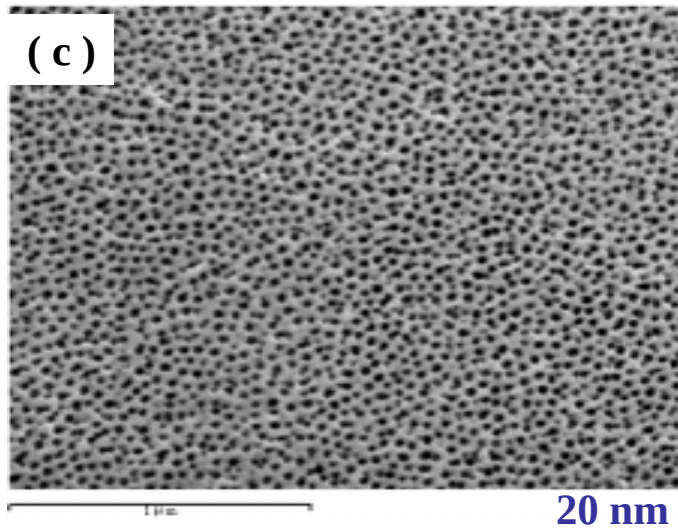
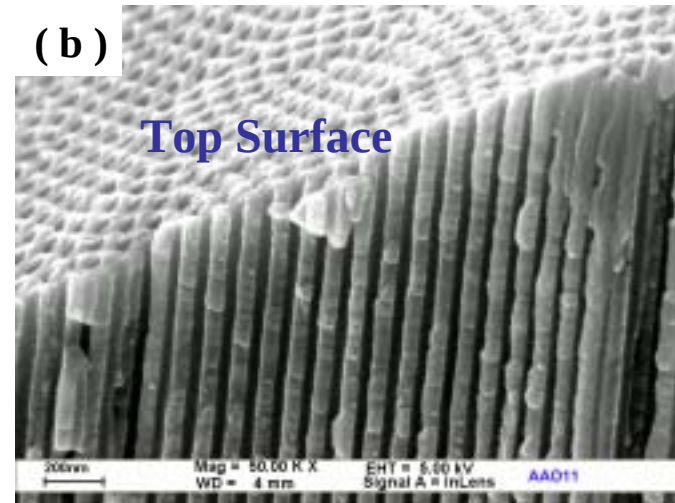
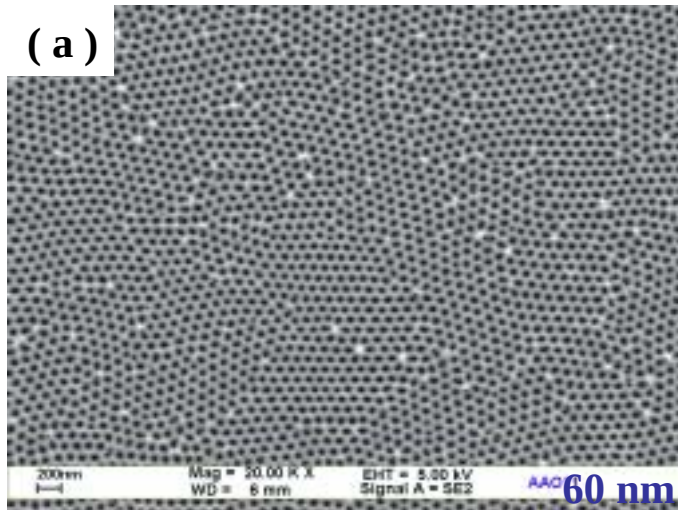
mesoporous materials, etc

# Nanowire Growth Mechanism

- Vapor-Liquid-Solid
- Melt injection into porous templates
- ✓ • Electrodeposition into porous templates

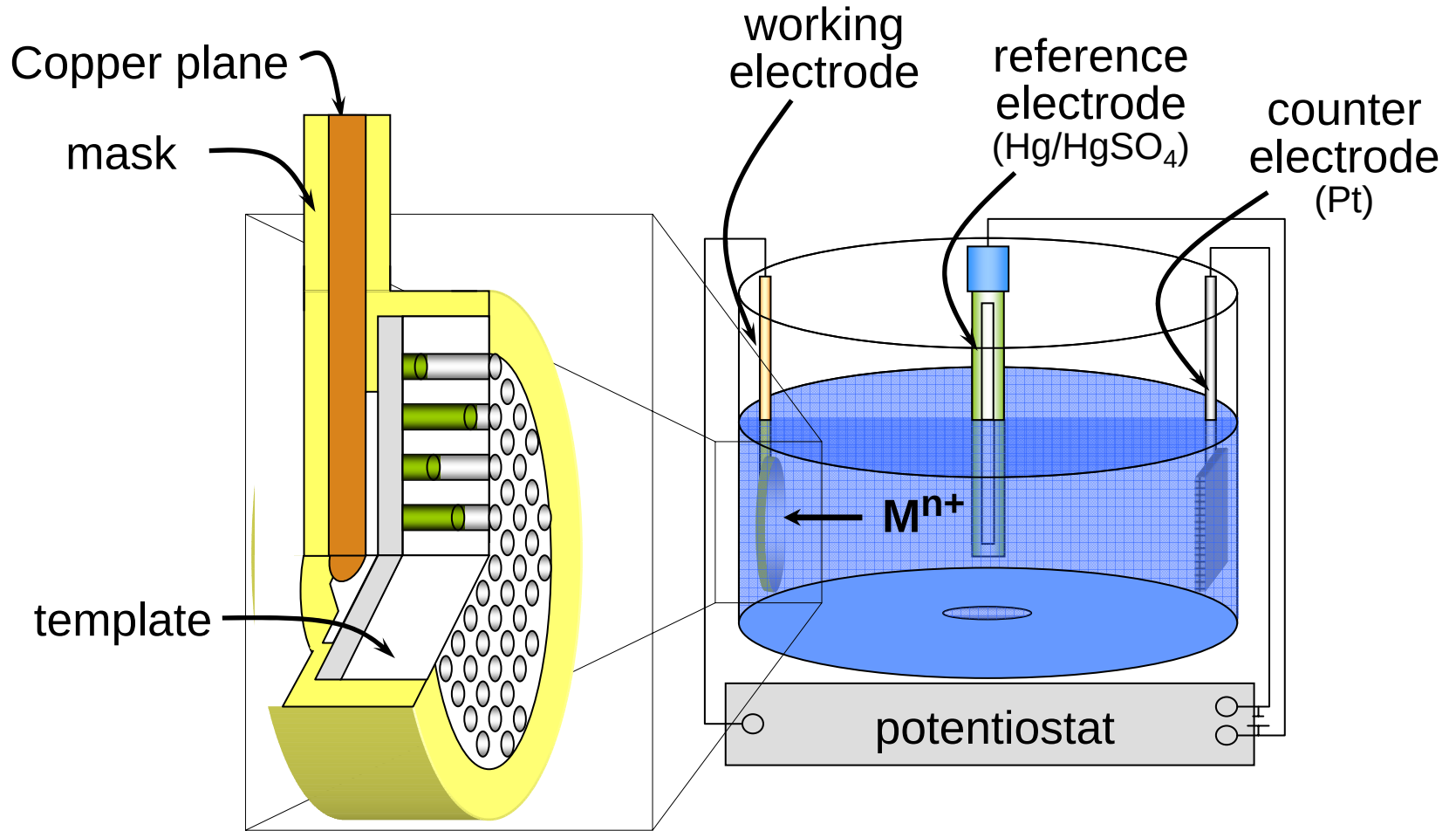
# Fabrication of Porous Anodic Alumina Templates





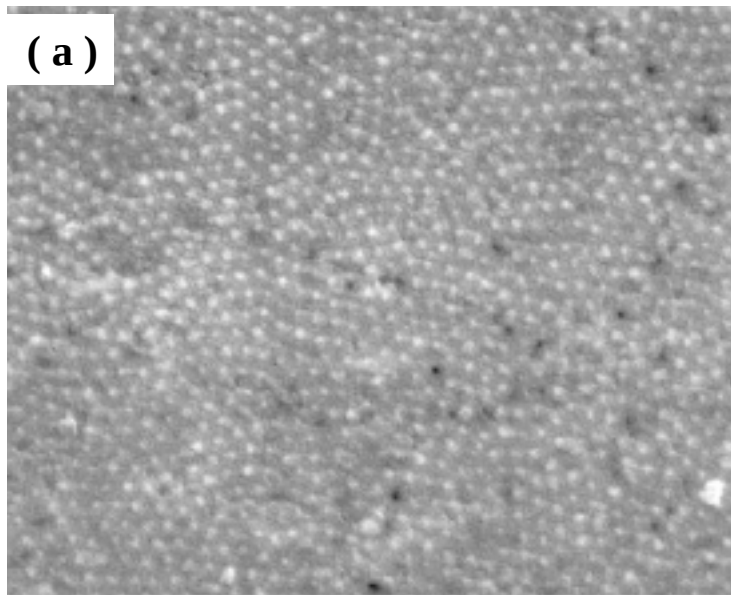
利用陽極處理氧化鋁 (Anodic Aluminum Oxide, AAO)製造各式尺寸的奈米孔洞模板, 孔洞的直徑分別為圖(a) 60nm (b)60nm nanopore template 的側面圖. (c)20nm (d) 10nm.

# Electrodeposition of Bi<sub>2</sub>Te<sub>3</sub> nanowire arrays

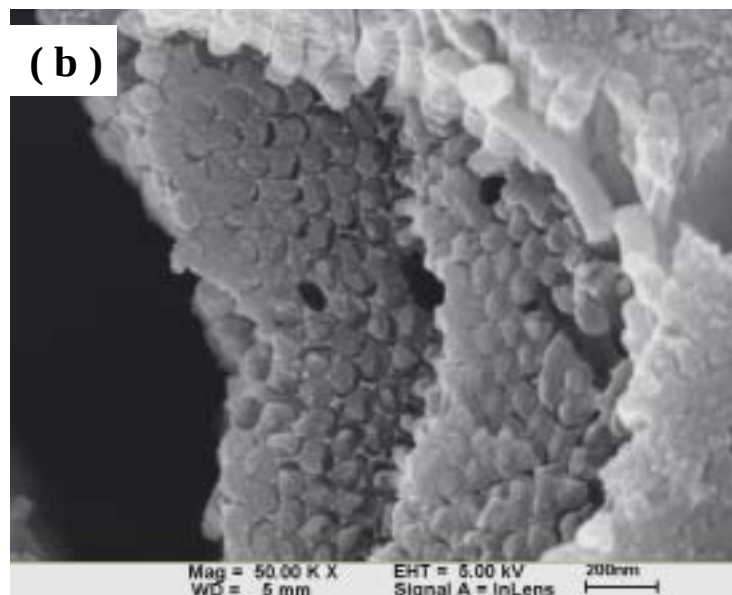




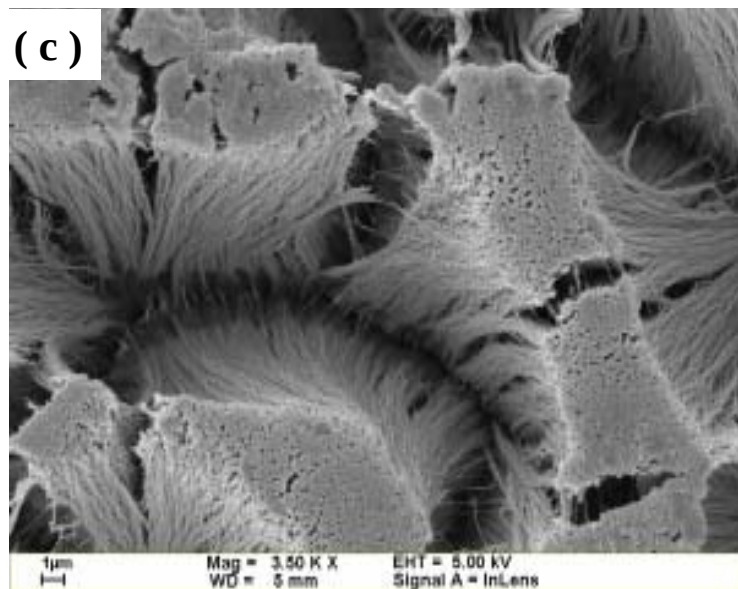
(a)



(b)



(c)



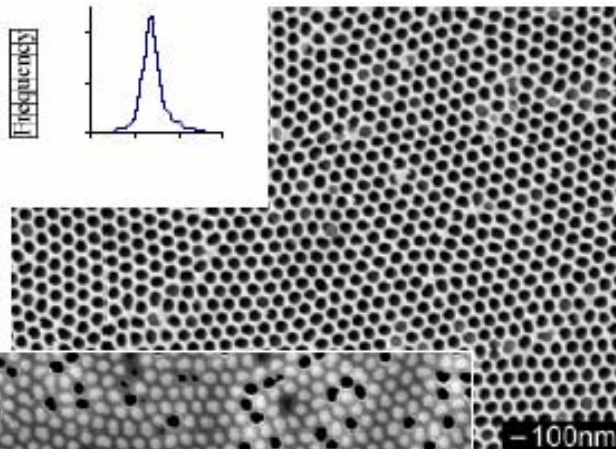
(d)



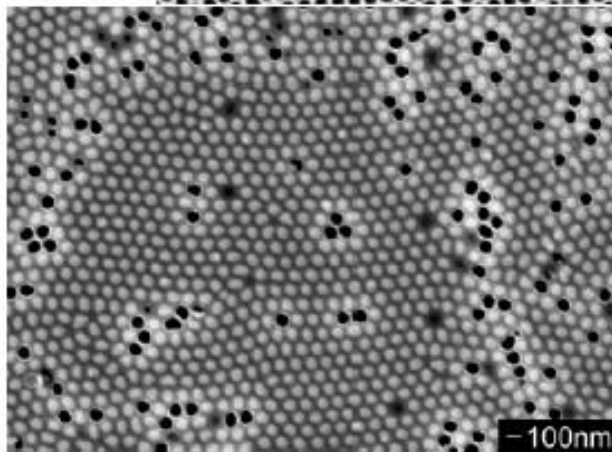
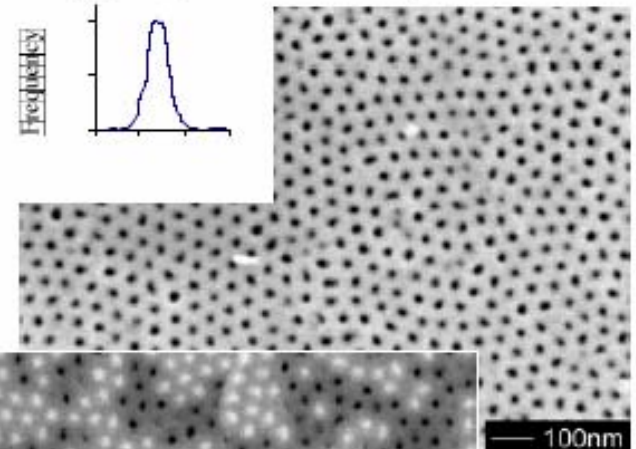
# Synthesis of $\text{Bi}_2\text{Te}_3$ /alumina nanocomposites

UC, Berkley

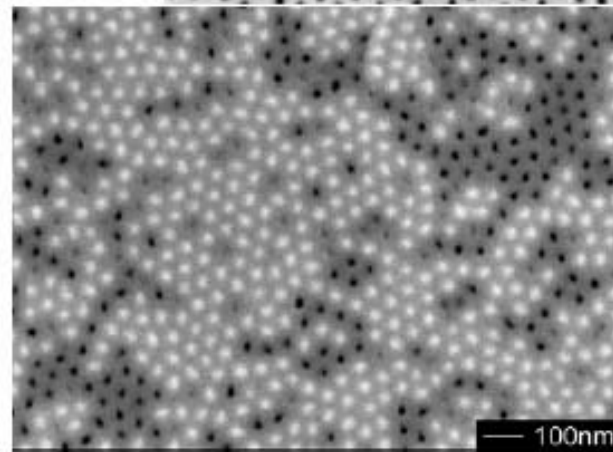
Empty template - 75 nm pore diameter



Empty template - 25 nm pore diameter

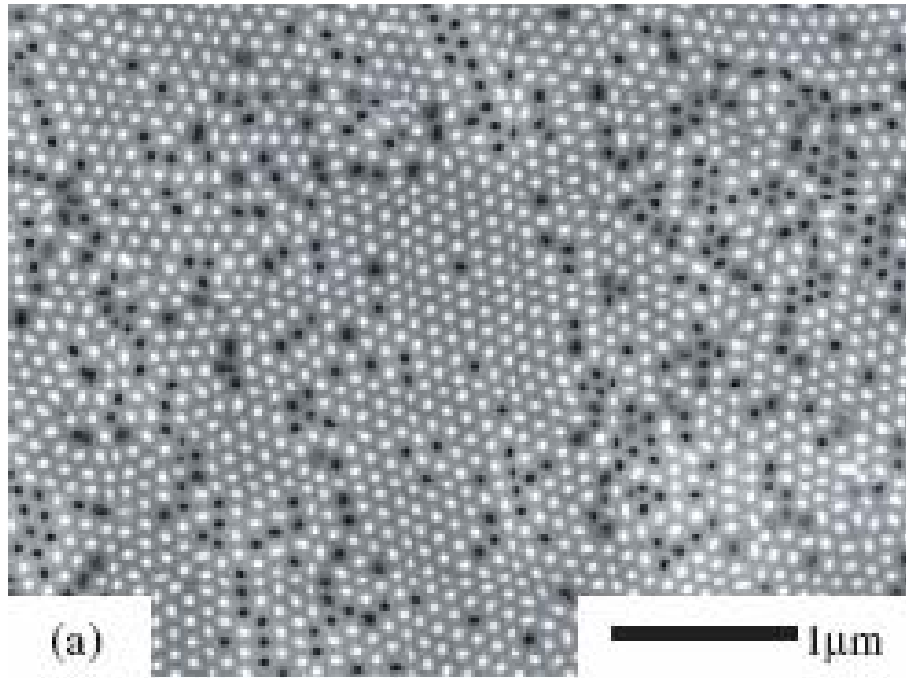


Filled template - 75 nm pore diameter

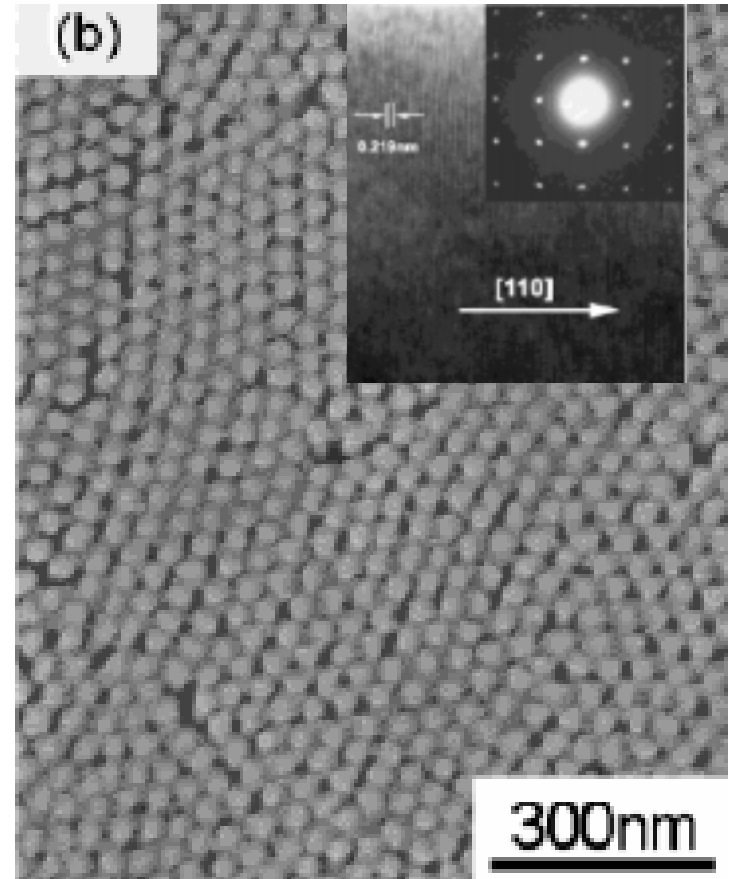


Filled template - 25 nm pore diameter

M.S. Sander, R. Gronsky, T. Sands, A.M. Stacy, "Structure of Bismuth Telluride Nanowire Arrays fabricated by Electrodeposition into Porous Anodic Alumina Templates," *Chem. Mater.* **15** (2003) pp. 335-39



Bi<sub>2</sub>Te<sub>3</sub> nanowire arrays (~45 nm)



Hexagonal Bi<sub>2</sub>Te<sub>3</sub> single-crystal  
Nanowires.

(Xiaoguang Li, *Hefei*, P. R. China)

*J. Phys. Chem. B* **2004**, 108, 1844-1847

(A. M. Stacy. Group, U. C. Berkeley. 2002)

# 6.2 Nanostuctured Crystals

- Natural Nanocrystal
- B12

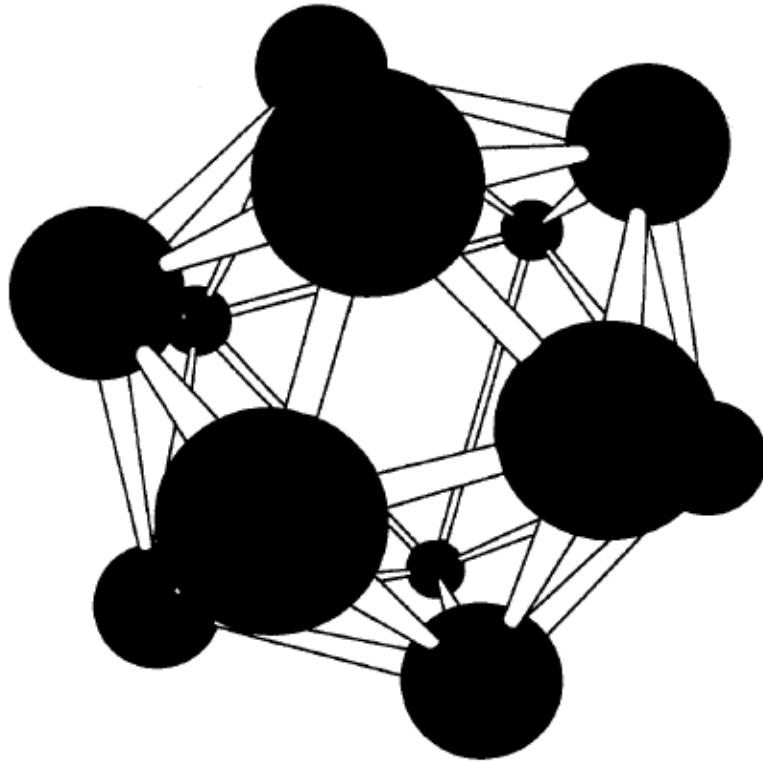


Figure 6.22. The icosahedral structure of a boron cluster containing 12 atoms. This is the basic unit of a number of boron lattices.

# Fullerene C<sub>60</sub>

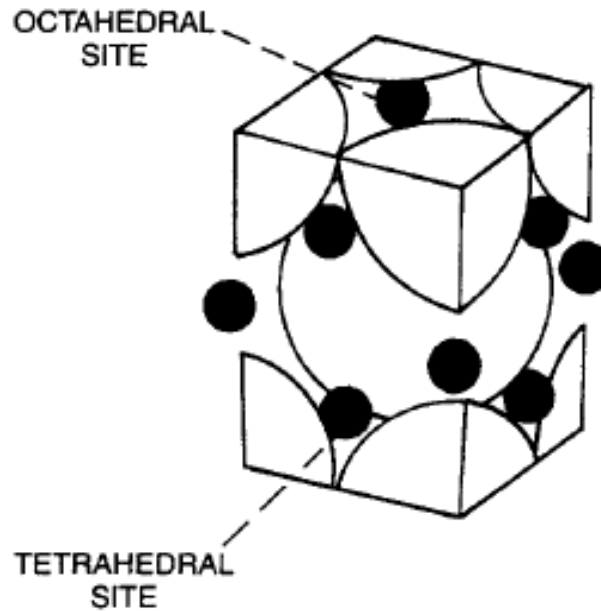
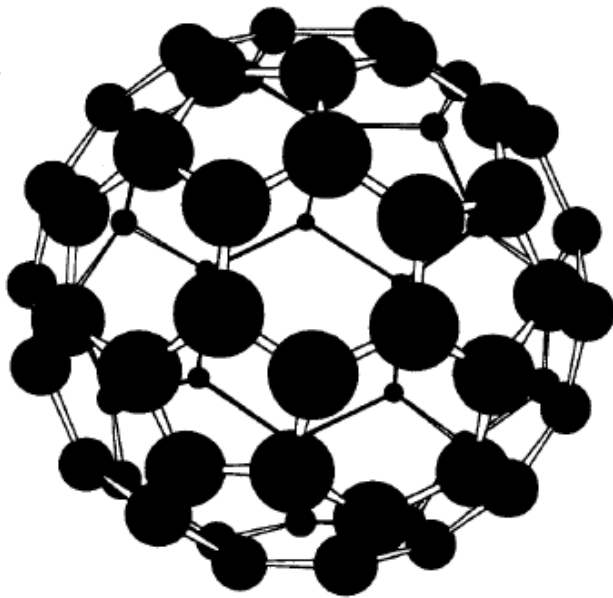


Figure 5.6. Structure of the C<sub>60</sub> fullerene molecule. Crystal lattice unit cell of C<sub>60</sub> molecules (large spheres) doped with alkali atoms